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 O.I.P.E.
 SCANNED TRF Q.A. GW

PATENT DATE	
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D. BLUM

Fumihiko Nakamura
Hisayoshi Kuramochi
Hiroji Kawai

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Insulating nitride layer and process for its forming, and semiconductor device and process for its production

PTO-2040
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<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS Sheets Drwg. Figs. Drwg. Print Fig.			CLAIMS ALLOWED Total Claims Print Claim for O.G.	
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